

# S-57TZ S Series

# AUTOMOTIVE, 150°C OPERATION, HIGH-WITHSTAND VOLTAGE, HIGH-SPEED, ZERO CROSSING LATCH HALL EFFECT IC

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Rev.1.1 00

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This IC, developed by CMOS technology, is a high-accuracy Hall effect IC that operates with high temperature and high-withstand voltage.

The IC switches output voltage level when the IC detects magnetic flux density (magnetic field) polarity changes. The Zero Crossing Latch detection method realizes polarity changes detection with the higher accuracy than the conventional bipolar latch method. Using this IC with a magnet makes it possible to detect the rotation status in various devices.

ABLIC Inc. offers a "magnetic simulation service" that provides the ideal combination of magnets and our Hall effect ICs for customer systems. Our magnetic simulation service will reduce prototype production, development period and development costs. In addition, it will contribute to optimization of parts to realize high cost performance. For more information regarding our magnetic simulation service, contact our sales representatives.

#### Caution This product can be used in vehicle equipment and in-vehicle equipment. Before using the product for these purposes, it is imperative to contact our sales representatives.

## Features

- Uses a thin (t0.80 mm max.) TSOT-23-3S or ultra-thin (t0.50 mm max.) HSNT-6(2025) package, allowing for device miniaturization
- Contributes to reduction of mechanism operation dispersion through high accuracy detection of magnetic flux density (magnetic field) polarity changes
- Suitable for devices which require high quality due to the production system of this IC which certifies automotive application quality
- Contributes to device safe design with a built-in reverse voltage protection circuit and output current limit circuit

## Specifications

Pole detection:	Zero Crossing Latch detection	DC brushless r
<ul> <li>Output logic<sup>*1</sup>:</li> </ul>	$V_{OUT}$ = "L" at S pole detection	automotive ap
	V <sub>OUT</sub> = "H" at S pole detection	<ul> <li>Automobile eq</li> </ul>
<ul> <li>Output form<sup>*1</sup>:</li> </ul>	Nch open-drain output	<ul> <li>Housing equips</li> </ul>
	Nch driver + built-in pull-up resistor (1.2 k $\Omega$ typ.)	<ul> <li>Industrial equip</li> </ul>
<ul> <li>Zero crossing latch point</li> </ul>	: Bz = 0.0 mT typ.	
<ul> <li>Release point (S pole)<sup>*1</sup>:</li> </ul>	B <sub>Rs</sub> = 3.0 mT typ.	
	B <sub>Rs</sub> = 6.0 mT typ.	
<ul> <li>Chopping frequency:</li> </ul>	$f_c = 500 \text{ kHz typ.}$	Packages
<ul> <li>Output delay time:</li> </ul>	t <sub>D</sub> = 8.0 μs typ.	-
<ul> <li>Power supply voltage rar</li> </ul>	nge*2: V <sub>DD</sub> = 2.7 V to 26.0 V	• TSOT-23-3S
<ul> <li>Built-in regulator</li> </ul>		• HSNT-6(2025)
<ul> <li>Built-in reverse voltage p</li> </ul>	protection circuit	
<ul> <li>Built-in output current lim</li> </ul>	nit circuit	
<ul> <li>Operation temperature ratio</li> </ul>	ange: Ta = $-40^{\circ}$ C to $+150^{\circ}$ C	
al and free (Sp 100%) he	logon frog	

- Lead-free (Sn 100%), halogen-free
- AEC-Q100 in process<sup>\*3</sup>
  - \*1. The option can be selected.
  - \*2.  $V_{DD}$  = 2.7 V to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.)
  - \*3. Contact our sales representatives for details.

## Applications

- motor for pplications
- quipment
- pment
- ipment

# S

# Block Diagrams

1. Nch open-drain output product



\*1. Parasitic diode



## 2. Nch driver + built-in pull-up resistor product



\*1. Parasitic diode

Figure 2

# ■ AEC-Q100 in Process

Contact our sales representatives for details of AEC-Q100 reliability specification.

# Product Name Structure

## 1. Product name



1: Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.)

\*1. Refer to the tape drawing.

### 2. Packages

 Table 1
 Package Drawing Codes

Package Name	Dimension	Таре	Reel	Land	Stencil Opening
TSOT-23-3S	MP003-E-P-SD	MP003-E-C-SD	MP003-E-R-SD	-	_
HSNT-6(2025)	PJ006-B-P-SD	PJ006-B-C-SD	PJ006-B-R-SD	PJ006-B-LM-SD	PJ006-B-LM-SD

## 3. Product name list

## 3.1 TSOT-23-3S

## Table 2

Product Name	Output Form	Power Supply Voltage Range	Output Logic	Release Point (S pole) (B <sub>RS</sub> )
S-57TZNL1S-L3T2U	Nch open-drain output	V <sub>DD</sub> = 2.7 V to 26.0 V	V <sub>OUT</sub> = "L" at S pole detection	3.0 mT typ.
S-57TZ1L1S-L3T2U	Nch driver + built-in pull-up resistor (1.2 k $\Omega$ typ.)	V <sub>DD</sub> = 2.7 V to 5.5 V	V <sub>OUT</sub> = "L" at S pole detection	3.0 mT typ.

**Remark** Please contact our sales representatives for products other than the above.

### 3.2 HSNT-6(2025)

## Table 3

Product Name	t Name Output Form Power Supply Voltage Range		Output Logic	Release Point (S pole) (B <sub>RS</sub> )
S-57TZNL1S-A6T8U	Nch open-drain output	V <sub>DD</sub> = 2.7 V to 26.0 V	V <sub>OUT</sub> = "L" at S pole detection	3.0 mT typ.
S-57TZ1L1S-A6T8U	Nch driver + built-in pull-up resistor (1.2 k $\Omega$ typ.)	V <sub>DD</sub> = 2.7 V to 5.5 V	$V_{OUT} = "L"$ at S pole detection	3.0 mT typ.

**Remark** Please contact our sales representatives for products other than the above.

## Pin Configurations

## 1. TSOT-23-3S

Top view



Table 4									
Pin No.	Symbol	Description							
1	VSS	GND pin							
2	VDD	Power supply pin							
3	OUT	Output pin							

Figure 3

## 2. HSNT-6(2025)



Figure 4

Table 5										
Pin No.	Symbol	Description								
1	VDD	Power supply pin								
2	NC <sup>*2</sup>	No connection								
3	OUT	Output pin								
4	NC <sup>*2</sup>	No connection								
5	VSS	GND pin								
6	NC <sup>*2</sup>	No connection								

- \*1. Connect the heatsink of backside at shadowed area to the board, and set electric potential open or GND. However, do not use it as the function of electrode.
- \*2. The NC pin is electrically open. The NC pin can be connected to the VDD pin or the VSS pin.

# Absolute Maximum Ratings

Table 6

Item			Absolute Maximum Rating	Unit	
	Nch open-drain output product		$V_{SS} - 28.0$ to $V_{SS} + 28.0$	V	
Power supply voltage	Nch driver + built-in pull-up resistor V (1.2 k $\Omega$ typ.) product		$V_{\text{SS}}-9.0$ to $V_{\text{SS}}+9.0$	V	
Power supply current		IDD	±10 m		
Output current	t louτ ±10			mA	
	Nch open-drain output product		$V_{\text{SS}}-0.3$ to $V_{\text{SS}}+28.0$	V	
Output voltage	Nch driver + built-in pull-up resistor (1.2 k $\Omega$ typ.) product	Vout	$V_{\text{SS}} - 0.3$ to $V_{\text{DD}} + 0.3$	V	
Junction temperature		T <sub>i</sub> -40 to +170			
Operation ambient tem	perature	Topr	-40 to +150	°C	
Storage temperature		T <sub>stg</sub>	-40 to +170	°C	

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

Table 7

# Thermal Resistance Value

Item	Symbol	Condition		Min.	Тур.	Max.	Unit
			Board A	-	225	-	°C/W
			Board B	1	190	_	°C/W
		TSOT-23-3S	Board C	I	_	-	°C/W
	ALθ		Board D	1	_	_	°C/W
lumetice to even is at the sum of versions are *1			Board E	I	_	-	°C/W
Junction-to-ambient thermal resistance*1			Board A	1	180	_	°C/W
			Board B	I	128	-	°C/W
		HSNT-6(2025)	Board C	I	43	-	°C/W
			Board D	-	44	_	°C/W
			Board E	-	36	_	°C/W

\*1. Test environment: compliance with JEDEC STANDARD JESD51-2A

**Remark** Refer to "**■ Power Dissipation**" and "**Test Board**" for details.

## Electrical Characteristics

## 1. Nch open-drain output product

Table 8

(Ta =  $-40^{\circ}$ C to  $+150^{\circ}$ C, V<sub>DD</sub> = 2.7 V to 26.0 V, V<sub>SS</sub> = 0 V unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.*1	Max.	Unit	Test Circuit
Power supply voltage	V <sub>DD</sub>	_	2.7	12.0	26.0	V	_
Current consumption	I <sub>DD</sub>	_	_	4.0	4.5	mA	1
Current consumption during reverse connection	I <sub>DDREV</sub>	V <sub>DD</sub> = -26.0 V	-0.1	-	I	mA	1
Low level output voltage	Vol	Ιουτ = 5 mA, Vουτ = "L"	-	-	0.4	V	2
Leakage current	ILEAK	V <sub>OUT</sub> = "H"	I	I	10	μA	3
Output limit current	Іом	V <sub>OUT</sub> = 12.0 V	11	I	35	mA	3
Output delay time*2	tD	_	_	8	16	μs	-
Chopping frequency*2	fc	_	250	500	-	kHz	-
Start up time*2	<b>t</b> PON	_	Ι	25	40	μs	4
Output rise time*2	t <sub>R</sub>	C = 20 pF, R = 820 Ω	_	_	1.0	μs	5
Output fall time*2	t⊧	C = 20 pF, R = 820 Ω	_	_	1.0	μs	5

\*1. Typ. value when Ta =  $+25^{\circ}$ C, V<sub>DD</sub> = 12.0 V.

\*2. This item is guaranteed by design.

## 2. Nch driver + built-in pull-up resistor (1.2 k $\Omega$ typ.) product

#### Table 9

(Ta =  $-40^{\circ}$ C to  $+150^{\circ}$ C, V<sub>DD</sub> = 2.7 V to 5.5 V, V<sub>SS</sub> = 0 V unless otherwise specified)

ltem	Symbol	Condition	Min.	Typ.*1	Max.	Unit	Test Circuit
Power supply voltage	V <sub>DD</sub>	_	2.7	5.0	5.5	V	-
Current consumption	IDD	V <sub>OUT</sub> = "H"	_	4.0	4.5	mA	1
Low level output voltage	Vol	Ιουτ = 0 mA, Vουτ = "L"	-	-	0.4	V	2
High level output voltage	Vон	Ιουτ = 0 mA, Vουτ = "H"	$V_{\text{DD}} \times 0.9$	-	-	V	2
Output limit current	I <sub>OM</sub>	$V_{DD} = V_{OUT} = 5.0 V$	11	-	35	mA	3
Output delay time*2	tD	_	_	8	16	μs	_
Chopping frequency*2	f <sub>C</sub>	_	250	500	-	kHz	_
Start up time*2	t <sub>PON</sub>	_	-	25	40	μs	4
Output rise time*2	t <sub>R</sub>	C = 20 pF	-		1.0	μs	5
Output fall time*2	t⊨	C = 20 pF	_	_	1.0	μs	5
Pull-up resistor	R∟	_	0.9	1.2	1.5	kΩ	_

\*1. Typ. value when Ta =  $+25^{\circ}$ C, V<sub>DD</sub> = 5.0 V.

\*2. This item is guaranteed by design.

Caution Due to limitation of the power dissipation, these values may not be satisfied. Attention should be paid to the power dissipation when using this IC in high temperature operation environments.



Figure 5 Operation Timing

## Magnetic Characteristics

## 1. TSOT-23-3S

1.1 Product with  $B_{RS} = 3.0 \text{ mT}$  typ.

#### Table 10

(Ta = +25°C, V <sub>DD</sub> = 5.0 V, V <sub>SS</sub> = 0 V unless otherwise specified									
Item		Symbol Condition Min. Typ. Max. Unit				Test Circuit			
Zero crossing latch po	oint	Bz*1 – –1.15 0.0 1.15 mT			mT	4			
Release point	S pole	B <sub>RS</sub> *2	_	1.9	3.0	4.1	mT	4	
	N pole	BRN*3	_	-4.1	-3.0	-1.9	mT	4	

#### 1. 2 Product with $B_{RS} = 6.0 \text{ mT}$ typ.

#### Table 11

#### (Ta = +25°C, V<sub>DD</sub> = 5.0 V, V<sub>SS</sub> = 0 V unless otherwise specified)

- - . . . .

Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Zero crossing latch point		Bz*1	_	-1.35	0.0	1.35	mT	4
	S pole	B <sub>RS</sub> *2	_	4.0	6.0	8.0	mT	4
Release point	N pole	B <sub>RN</sub> *3	_	-8.0	-6.0	-4.0	mT	4

#### 2. HSNT-6(2025)

#### 2.1 Product with $B_{RS} = 3.0 \text{ mT}$ typ.

Table 12

			(Ta = +25	°C, V <sub>DD</sub> = 8	5.0 V, Vss :	= 0 V unles	s otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Zero crossing latch point		Bz*1	_	-1.65	0.0	1.65	mT	4
Delesses weight	S pole	B <sub>RS</sub> *2	_	1.0	3.0	5.0	mT	4
Release point	N pole	B <sub>RN</sub> *3	_	-5.0	-3.0	-1.0	mT	4

#### 2. 2 Product with $B_{RS} = 6.0 \text{ mT}$ typ.

#### Table 13

			(Ta = +25	°C, V <sub>DD</sub> = {	5.0 V, V <sub>SS</sub> :	= 0 V unles	ss otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Zero crossing latch point		Bz*1	_	-1.75	0.0	1.75	mT	4
Delesses weint	S pole	B <sub>RS</sub> *2	_	3.5	6.0	8.5	mT	4
Release point	N pole	B <sub>RN</sub> *3	-	-8.5	-6.0	-3.5	mT	4

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\*1. B<sub>Z</sub>: Zero crossing latch point
 B<sub>Z</sub> is the value of magnetic flux density at which polarity changes are detected according to the magnetic flux density applied to this IC.

 \*2. B<sub>RS</sub> : Release point (S pole) B<sub>RS</sub> is the value of magnetic flux density of release point (S pole). This IC releases the Hold status of the output voltage (V<sub>OUT</sub>) when the magnetic flux density applied to this IC exceeds B<sub>RS</sub> (by moving the magnet (S pole) closer).

#### \*3. $B_{RN}$ : Release point (N pole) $B_{RN}$ is the value of magnetic flux density of release point (N pole).

This IC releases the Hold status of the output voltage ( $V_{OUT}$ ) when the magnetic flux density applied to this IC exceeds B<sub>RN</sub> (by moving the magnet (N pole) closer).

**Remark** The unit of magnetic density mT can be converted by using the formula 1 mT = 10 Gauss.

# Test Circuits



\*1. Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.





Figure 8 Test Circuit 3



built-in pull-up resistor product.

Figure 10 Test Circuit 5







\*1. Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.

### Figure 9 Test Circuit 4

# Standard Circuit



\*1. Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.

Figure 11

Caution The above connection diagram and constants will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constants.

# Operation

## 1. Direction of applied magnetic flux

This IC detects the magnetic flux density which is perpendicular to the package marking surface. A magnetic field is defined as positive when marking side of the package is the S pole, and negative when it is the N pole. **Figure 12** and **Figure 13** show polarity in a magnetic field and direction in which magnetic flux is being applied.

#### 1.1 TSOT-23-3S





### 2. Position of Hall sensor

Figure 14 and Figure 15 show the position of Hall sensor.

The center of this Hall sensor is located in the area indicated by a circle, which is in the center of a package as described below.

The following also shows the distance (typ. value) between the marking surface and the chip surface of a package.

#### 2.1 TSOT-23-3S

#### 2.2 HSNT-6(2025)



#### 3. Basic operation

This IC switches output voltage level ( $V_{OUT}$ ) when the IC detects magnetic flux density (magnetic field) polarity changes by using Zero Crossing Latch technology. Zero Crossing Latch technology realizes polarity changes detection and hold operation (Hold status) of  $V_{OUT}$ . This is different from the conventional bipolar latch method. Zero Crossing Latch detection method has no hysteresis width of the magnetic sensitivity to switch  $V_{OUT}$ . Instead, the Zero Crossing Latch detection method can switch  $V_{OUT}$  without chattering by using the Hold status.

#### 3.1 Zero Crossing Latch basic operation

This IC switches  $V_{OUT}$  after the output delay time (t<sub>D</sub>) from when the magnetic flux density applied to this IC crosses B<sub>Z</sub> (from B > B<sub>RS</sub> to B < B<sub>Z</sub> or from B < B<sub>RN</sub> to B > B<sub>Z</sub>). When V<sub>OUT</sub> is switched, this IC starts the Hold status. In the Hold status of V<sub>OUT</sub>, when the magnetic flux density applied to this IC exceeds B<sub>RS</sub> or B<sub>RN</sub>, this IC releases the Hold status (from B < B<sub>Z</sub> to B < B<sub>RN</sub> or from B > B<sub>Z</sub> to B > B<sub>RS</sub>).

Figure 16 and Figure 17 show the  $V_{OUT}$  operation timing when sine wave magnetic flux density is applied to this IC.

- (1)  $B > B_{RS} \rightarrow B < B_Z$ , and after t<sub>D</sub>, V<sub>OUT</sub> = "L"  $\rightarrow$  "H", and Hold status starts
- (2)  $B < B_Z \rightarrow B < B_{RN}$ , and after t<sub>D</sub>, Hold status is released, and V<sub>OUT</sub> = "H" continues
- (3)  $B < B_{RN} \rightarrow B > B_Z$ , and after t<sub>D</sub>, V<sub>OUT</sub> = "H"  $\rightarrow$  "L", and Hold status starts
- (4)  $B > B_Z \rightarrow B > B_{RS}$ , and after t<sub>D</sub>, Hold status is released, and V<sub>OUT</sub> = "L" continues



Figure 16 Product with VOUT = "L" at S pole detection

# AUTOMOTIVE, 150°C OPERATION, HIGH-WITHSTAND VOLTAGE, HIGH-SPEED, ZERO CROSSING LATCH HALL EFFECT IC S-57TZ S Series Rev.1.1\_00

- (1)  $B > B_{RS} \rightarrow B < B_Z$ , and after t<sub>D</sub>, V<sub>OUT</sub> = "H"  $\rightarrow$  "L", and Hold status starts
- (2)  $B < B_Z \rightarrow B < B_{RN}$ , and after t<sub>D</sub>, Hold status is released, and V<sub>OUT</sub> = "L" continues
- (3)  $B < B_{RN} \rightarrow B > B_Z,$  and after  $t_D,$   $V_{OUT}$  = "L"  $\rightarrow$  "H", and Hold status starts
- (4)  $B > B_Z \rightarrow B > B_{RS}$ , and after t<sub>D</sub>, Hold status is released, and V<sub>OUT</sub> = "H" continues



Figure 17 Product with VOUT = "H" at S pole detection

#### 3. 2 Prevention of VOUT chattering by Hold status

By the Hold status, this IC can switch V<sub>OUT</sub> without chattering even under an influence of external mechanical vibrations, electrical noise, or magnetic noise.

**Figure 18** and **Figure 19** show the V<sub>OUT</sub> operation when the magnetic flux density applied to this IC changes near the zero crossing latch point (B<sub>z</sub>) and B<sub>z</sub> is crossed multiple times.

(1) In the Hold status, the IC retains VOUT when the magnetic flux density applied to this IC crosses Bz.



Figure 18 Product with V<sub>OUT</sub> = "L" at S pole detection



Figure 19 Product with V<sub>OUT</sub> = "H" at S pole detection

#### 3.3 Operation when polarity changes direction is inverted in the Hold status

In the Hold status, when the polarity changes direction is inverted, this IC release the Hold status at the opposite release point and switches  $V_{\text{OUT}}$ .

Figure 20 and Figure 21 show the VOUT operation timing when the polarity change direction is inverted.

- (1)  $B > B_Z \rightarrow B < B_Z$ , and after t<sub>D</sub>, V<sub>OUT</sub> = "L"  $\rightarrow$  "H", and Hold status starts
- (2) During Hold status, even after  $B < B_Z \rightarrow B > B_Z$ ,  $V_{OUT} = "H"$  is retained
- (3)  $B > B_Z \rightarrow B > B_{RS}$ , and after t<sub>D</sub>, Hold status is released, and V<sub>OUT</sub> = "H"  $\rightarrow$  "L"
- (4)  $B < B_Z \rightarrow B > B_Z,$  and after  $t_D,$   $V_{OUT}$  = "H"  $\rightarrow$  "L", and Hold status starts
- (5) During Hold status, even after  $B > B_Z \rightarrow B < B_Z$ ,  $V_{OUT}$  = "L" is retained
- (6)  $B < B_Z \rightarrow B < B_{RN}$ , and after t<sub>D</sub>, Hold status is released, and V<sub>OUT</sub> = "L"  $\rightarrow$  "H"



Figure 20 Product with V<sub>OUT</sub> = "L" at S pole detection

- (1)  $B > B_Z \rightarrow B < B_Z,$  and after  $t_D, \, V_{OUT}$  = "H"  $\rightarrow$  "L", and Hold status starts
- (2) During Hold status, even after  $B < B_Z \rightarrow B > B_Z$ ,  $V_{OUT}$  = "L" is retained
- (3)  $B > B_Z \rightarrow B > B_{RS},$  and after  $t_D,$  Hold status is released, and  $V_{OUT}$  = "L"  $\rightarrow$  "H"
- (4)  $B < B_Z \rightarrow B > B_Z,$  and after  $t_D, \, V_{OUT}$  = "L"  $\rightarrow$  "H", and Hold status starts
- (5) During Hold status, even after  $B > B_Z \rightarrow B < B_Z, V_{\text{OUT}}$  = "H" is retained
- (6)  $B < B_Z \rightarrow B < B_{RN},$  and after  $t_D,$  Hold status is released, and  $V_{OUT}$  = "H"  $\rightarrow$  "L"



Figure 21 Product with V<sub>OUT</sub> = "H" at S pole detection

#### 4. Power-on operation

This IC requires start up time (t<sub>PON</sub>) during the time immediately after power-on until V<sub>OUT</sub> switches. During the t<sub>PON</sub> period, V<sub>OUT</sub> is "H". After t<sub>PON</sub>, when B > B<sub>RS</sub> or B < B<sub>RN</sub> is detected, polarity changes can be detected.

#### 4.1 $B > B_{RS}$ or $B < B_{RN}$

When the magnetic flux density applied to this IC at power-on is  $B > B_{RS}$  or  $B < B_{RN}$ , after t<sub>PON</sub>, V<sub>OUT</sub> switches according to the output logic at the S pole detection, and polarity changes can be detected. **Figure 22** and **Figure 23** show V<sub>OUT</sub> operation immediately after power-on when  $B > B_{RS}$  or  $B < B_{RN}$ .







Figure 23 Product with VOUT = "H" at S pole detection

#### 4.2 B<sub>RN</sub> < B < B<sub>RS</sub>

When the magnetic flux density applied to this IC at power-on is  $B_{RN} < B < B_{RS}$ , after  $t_{PON}$ ,  $V_{OUT}$  continues "H". Thereafter, when the magnetic flux density changes to  $B > B_{RS}$  or  $B < B_{RN}$ , after  $t_D$ ,  $V_{OUT}$  switches according to the output logic at the S pole detection and magnetic flux density, and polarity changes can be detected. **Figure 24** and **Figure 25** show  $V_{OUT}$  operation when change of  $B_{RN} < B < B_{RS} \rightarrow B > B_{RS}$  or  $B < B_{RN}$  occurs after  $t_{PON}$ .









## Precautions

- If the impedance of the power supply is high, the IC may malfunction due to a supply voltage drop caused by feed-through current. Take care with the pattern wiring to ensure that the impedance of the power supply is low.
- Note that the IC may malfunction if the power supply voltage rapidly changes. When the IC is used under the
  environment where the power supply voltage rapidly changes, it is recommended to judge the output voltage of
  the IC by reading it multiple times.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- Although this IC has a built-in output current limit circuit, it may suffer physical damage such as product deterioration under the environment where the absolute maximum ratings are exceeded.
- Although this IC has a built-in reverse voltage protection circuit, it may suffer physical damage such as product deterioration under the environment where the absolute maximum ratings are exceeded.
- The application conditions for the power supply voltage, the pull-up voltage, and the pull-up resistor should not exceed the power dissipation.
- Large stress on this IC may affect the magnetic characteristics. Avoid large stress which is caused by the handling during or after mounting the IC on a board.
- Since the package heat radiation differs according to the conditions of the application, perform thorough evaluation with actual applications to confirm no problems occur.
- ABLIC Inc. claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

## Characteristics (Typical Data)

#### 1. Electrical Characteristics

1.1 S-57TZxxxS



Caution  $V_{DD}$  = 2.7 V to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.). Comply with power supply voltage range and do not exceed absolute maximum ratings.

#### 1.2 S-57TZNxxS

1. 2. 1 Low level output voltage (V<sub>OL</sub>) vs. Temperature (Ta)



1. 2. 2 Low level output voltage (V<sub>OL</sub>) vs. Power supply voltage (V<sub>DD</sub>)



## 1.3 S-57TZ1xxS









1. 3. 2 Low level output voltage (V<sub>OL</sub>) vs. Power supply voltage (V<sub>DD</sub>)



1.3.4 High level output voltage (V<sub>OH</sub>) vs. Power supply voltage (V<sub>DD</sub>)



#### 2. Magnetic Characteristics

#### 2.1 S-57TZxx1S-L3T2U

2. 1. 1 Zero crossing latch point (Bz) vs. Temperature (Ta)











2. 1. 2 Zero crossing latch point (Bz) vs. Power supply voltage (V<sub>DD</sub>)



2. 1. 4 Zero crossing latch point (B<sub>Z</sub>) vs. Power supply voltage (V<sub>DD</sub>)







Caution  $V_{DD} = 2.7$  V to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.). Comply with power supply voltage range and do not exceed absolute maximum ratings.

#### 2. 2 S-57TZxx2S-L3T2U











2. 2. 2 Zero crossing latch point (Bz) vs. Power supply voltage (V<sub>DD</sub>)











Caution  $V_{DD} = 2.7$  V to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.). Comply with power supply voltage range and do not exceed absolute maximum ratings.

#### 2.3 S-57TZxx1S-A6T8U























Caution  $V_{DD} = 2.7$  V to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.). Comply with power supply voltage range and do not exceed absolute maximum ratings.

#### 2.4 S-57TZxx2S-A6T8U











2. 4. 2 Zero crossing latch point (Bz) vs. Power supply voltage (V<sub>DD</sub>)











Caution  $V_{DD} = 2.7 \text{ V}$  to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.). Comply with power supply voltage range and do not exceed absolute maximum ratings.

## Power Dissipation

## **TSOT-23-3S**

## HSNT-6(2025)



Board	Power Dissipation (P <sub>D</sub> )
А	0.64 W
В	0.76 W
С	_
D	_
E	_



Ambient temperature (Ta) [°C]

Board	Power Dissipation (P <sub>D</sub> )
А	0.81 W
В	1.13 W
С	3.37 W
D	3.30 W
E	4.03 W

# TSOT-23-3S Test Board

IC Mount Area

# (1) Board A



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
	1	Land pattern and wiring for testing: t0.070
Copper foil layer [mm]	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

# (2) Board B



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
	1	Land pattern and wiring for testing: t0.070
Connor foil lover [mm]	2	74.2 x 74.2 x t0.035
Copper foil layer [mm]	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

No. TSOT23x-A-Board-SD-1.0

# HSNT-6(2025) Test Board

# IC Mount Area

# (1) Board A



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
	1	Land pattern and wiring for testing: t0.070
Copper foil layer [mm]	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

(2) Board B



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

# (3) Board C



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
	1	Land pattern and wiring for testing: t0.070
Copper foil layer [mm]	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		Number: 4 Diameter: 0.3 mm

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enlarged view

# No. HSNT6-B-Board-SD-1.0

# HSNT-6(2025) Test Board

# ) IC Mount Area

# (4) Board D



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
	1	Pattern for heat radiation: 2000mm <sup>2</sup> t0.070
Coppor foil lover [mm]	2	74.2 x 74.2 x t0.035
Copper foil layer [mm]	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-



## (5) Board E



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
	1	Pattern for heat radiation: 2000mm <sup>2</sup> t0.070
Copper foil layer [mm]	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		Number: 4 Diameter: 0.3 mm



enlarged view

No. HSNT6-B-Board-SD-1.0







No. MP003-E-P-SD-1.0

TITLE	TSOT233S-A-PKG Dimensions			
No.	MP003-E-P-SD-1.0			
ANGLE	$\odot$			
UNIT	mm			
ABLIC Inc.				







## No. PJ006-B-P-SD-1.0

TITLE	HSNT-6-C-PKG Dimensions
No.	PJ006-B-P-SD-1.0
ANGLE	$\bigoplus \Box$
UNIT	mm
ABLIC Inc.	



TITLE	HSNT-6-C-Carrier Tape	
No.	PJ006-B-C-SD-1.0	
ANGLE		
UNIT	mm	
ABLIC Inc.		





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